

100V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

$V_{(BR)DSS}$	Max $R_{DS(on)}$	Max I_D $T_A = 25^\circ C$ (Note 5)
100V	250m Ω @ $V_{GS} = 10V$	1.9A
	300m Ω @ $V_{GS} = 6V$	1.68A

Description and Applications

This MOSFET features a unique structure, combining the benefits of low on-resistance and fast switching, making it ideal for high-efficiency, power management applications.

- DC - DC Converters
- Power Management Functions
- Disconnect Switches
- Motor Control

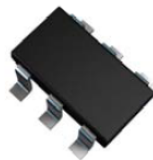
Features and Benefits

- Low On-Resistance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

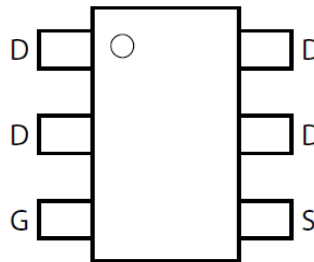
Mechanical Data

- Case: SOT26
- Case Material: Molded Plastic, "Green" Molding Compound.
UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe.
Solderable per MIL-STD-202, Method 208②③
- Weight: 0.015 grams (Approximate)

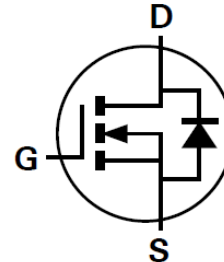
SOT26



Top View



Pinout Top-view



Device symbol

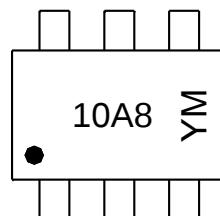
Ordering Information (Note 4)

Part Number	Reel Size (inch)	Tape Width (mm)	Quantity Per Reel
ZXMN10A08E6TA	7	8	3000
ZXMN10A08E6TC	13	8	10,000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com>.

Marking Information

SOT26



10A8 = Product Type Marking Code
YM = Date Code Marking
Y or $\bar{Y}$ = Year (ex: C = 2015)
M or $\bar{M}$ = Month (ex: 9 = September)

Date Code Key

Year	2015	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025
Code	C	D	E	F	G	H	I	J	K	L	M

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

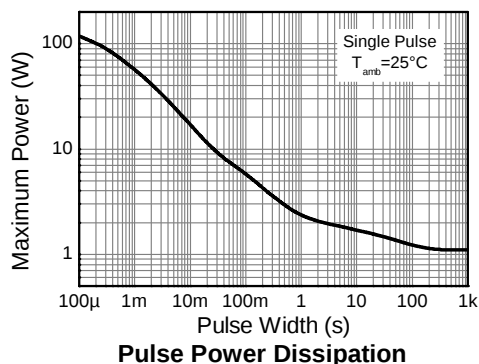
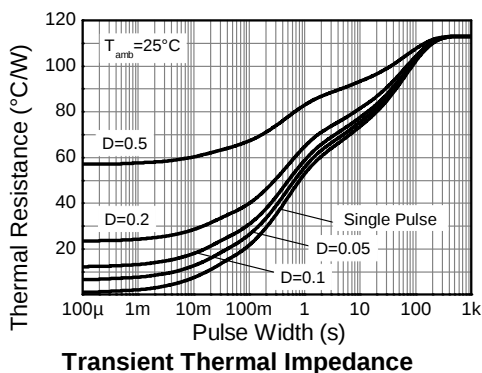
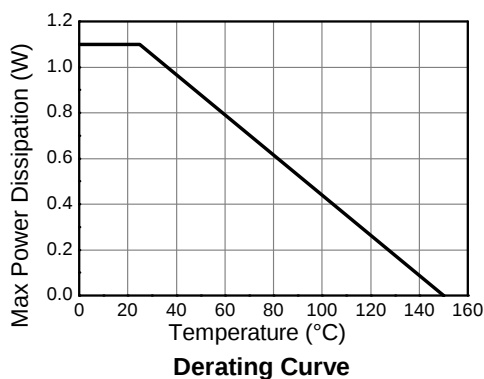
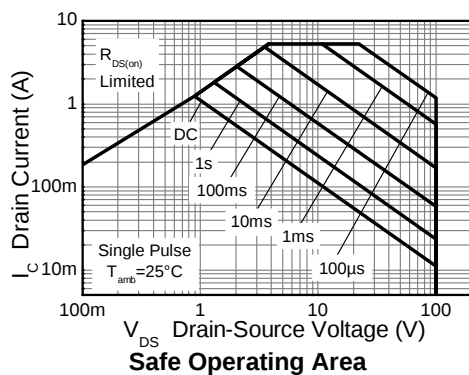
Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	100	V
Gate-Source Voltage			V _{GS}	±20	V
Continuous Drain Current	V _{GS} = 10V	Note 5)	I _D	1.9	A
		T _A =+70°C (Note 5)		1.5	
		(Note 4)		1.5	
		(Note 7)		3.5	
Pulsed Drain Current		(Note 6)	I _{DM}	8.6	A
Continuous Source Current (Body Diode)		(Note 5)	I _S	2.5	A
Pulsed Source Current (Body Diode)		(Note 6)	I _{SM}	8.6	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 4)	P _D	1.1	W
	(Note 5)		1.7	
	(Note 7)		6.3	
	(Note 4)		114	
Thermal Resistance, Junction to Ambient	(Note 5)	R _{θJA}	73.5	°C/W
	(Note 7)		19.7	
Thermal Resistance, Junction to Leads	(Note 7)	R _{θJL}	19.7	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

- Notes:
4. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
 5. For a device surface mounted on FR4 PCB measured at t ≤ 5 sec.
 6. Repetitive rating 25mm x 25mm FR4 PCB, D = 0.02, pulse width 300μs - pulse width limited by maximum junction temperature.
 7. Thermal resistance from junction to solder-point (at the end of the drain lead).

Thermal Characteristics

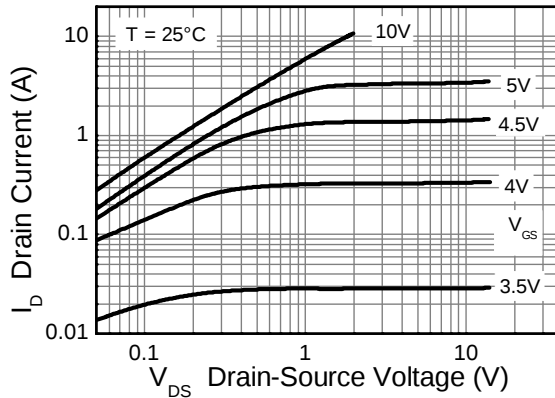


Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

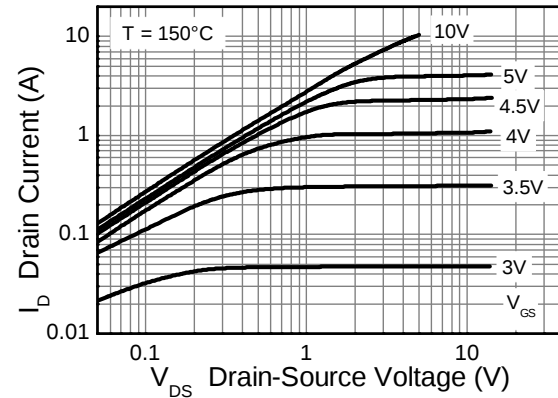
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	100	—	—	V	I _D = 250μA, V _{GS} = 0V
Zero Gate Voltage Drain Current	I _{DSS}	—	—	0.5	μA	V _{DS} = 100V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(th)}	2.0	—	4.0	V	I _D = 250μA, V _{DS} = V _{GS}
Static Drain-Source On-Resistance (Note 8)	R _{DS (ON)}	—	—	0.25	Ω	V _{GS} = 10V, I _D = 3.2A
				0.30		V _{GS} = 6V, I _D = 2.6A
Forward Transconductance (Notes 8 & 10)	g _{fs}	—	5.0	—	S	V _{DS} = 15V, I _D = 3.2A
Diode Forward Voltage (Note 8)	V _{SD}	—	0.87	0.95	V	I _S = 3.2A, V _{GS} = 0V
Reverse Recovery Time (Note 10)	t _{rr}	—	27	—	ns	I _S = 1.2A, di/dt = 100A/μs
Reverse Recovery Charge (Note 10)	Q _{rr}	—	32	—	nC	
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C _{iss}	—	405	—	pF	V _{DS} = 50V, V _{GS} = 0V f = 1MHz
Output Capacitance	C _{oss}	—	28.2	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	14.2	—	pF	
Gate Charge (Note 9)	Q _g	—	4.2	—	nC	V _{GS} = 5V, V _{DS} = 50V I _D = 1.2A
Total Gate Charge (Note 9)	Q _g	—	7.7	—	nC	V _{GS} = 10V, V _{DS} = 50V I _D = 1.2A
Gate-Source Charge (Note 9)	Q _{gs}	—	1.8	—	nC	
Gate-Drain Charge (Note 9)	Q _{gd}	—	2.1	—	nC	
Turn-On Delay Time (Note 9)	t _{d(on)}	—	3.4	—	ns	V _{DD} = 30V, V _{GS} = 10V I _D = 1.2A, R _G ≐ 6.0Ω
Turn-On Rise Time (Note 9)	t _r	—	2.2	—	ns	
Turn-Off Delay Time (Note 9)	t _{d(off)}	—	8	—	ns	
Turn-Off Fall Time (Note 9)	t _f	—	3.2	—	ns	

Notes: 8. Measured under pulsed conditions. Width ≤300μs. Duty cycle ≤2%.
9. Switching characteristics are independent of operating junction temperature.
10. For design aid only, not subject to production testing.

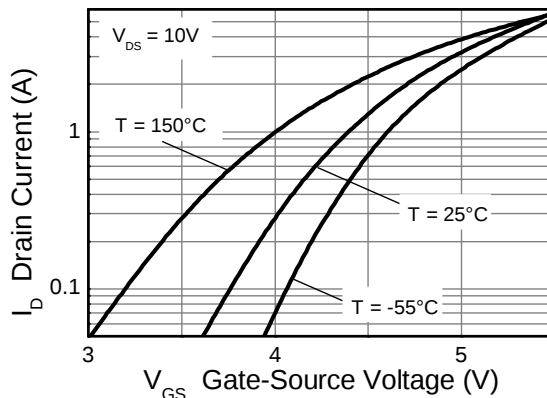
Typical Characteristics



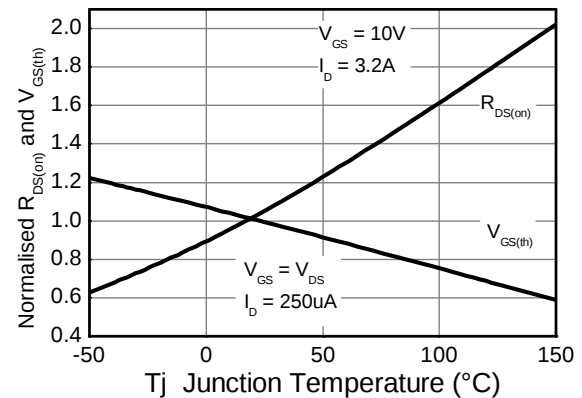
Output Characteristics



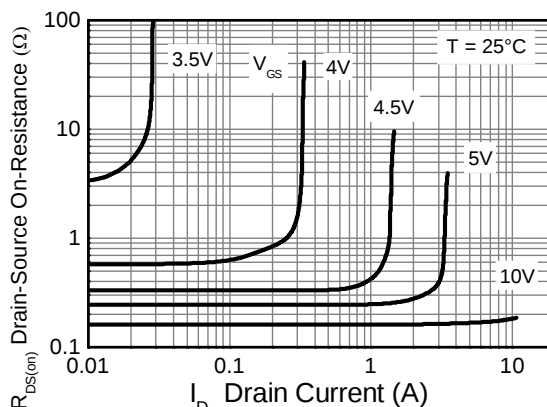
Output Characteristics



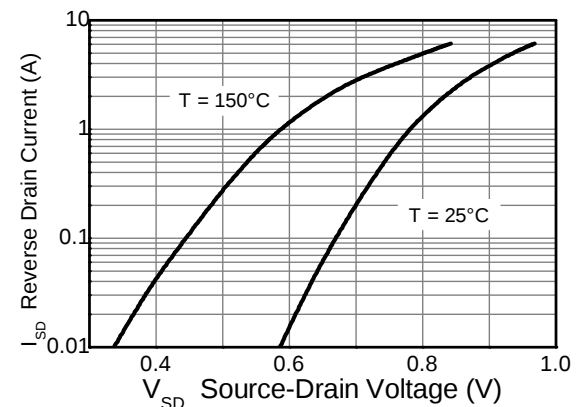
Typical Transfer Characteristics



Normalised Curves v Temperature

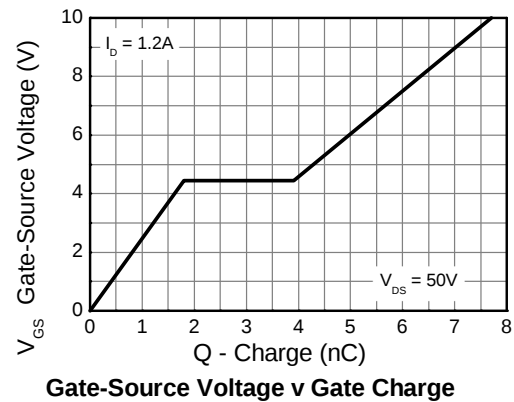
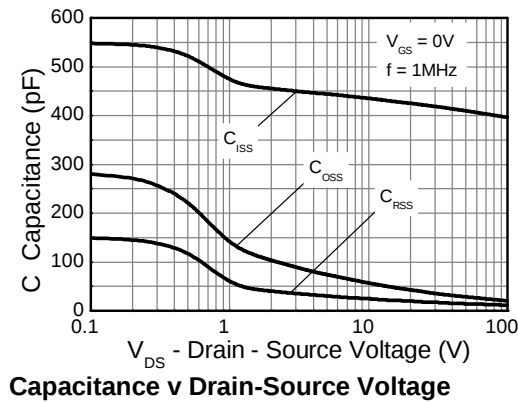


On-Resistance v Drain Current

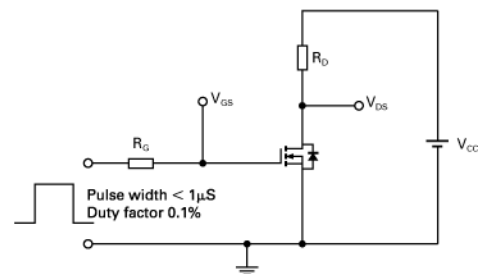
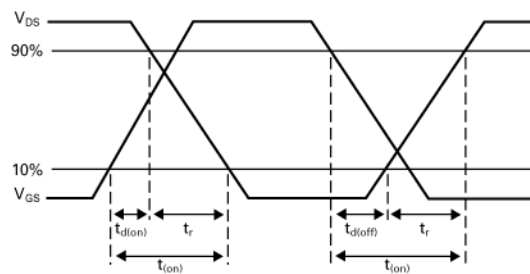
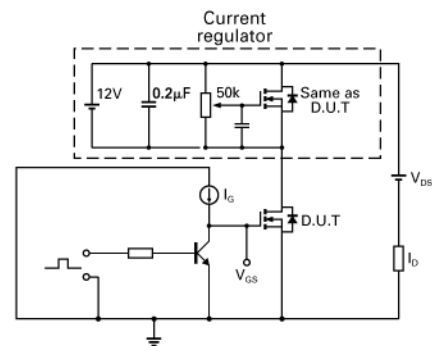
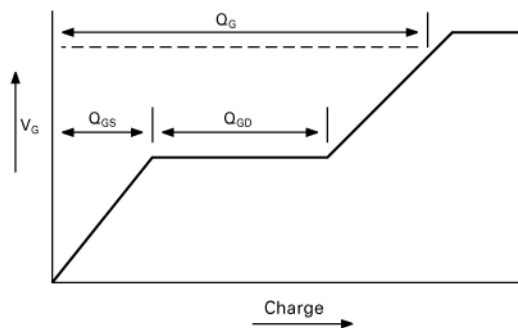


Source-Drain Diode Forward Voltage

Typical Characteristics (continued)

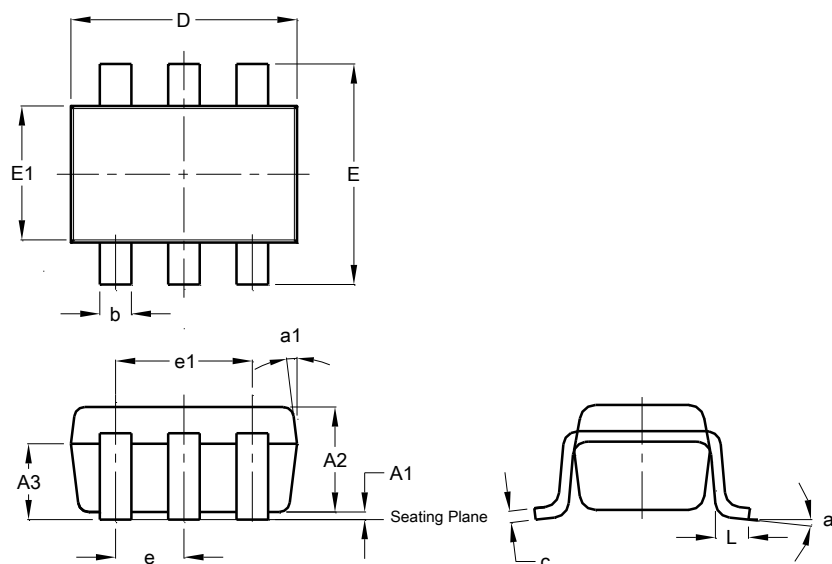


Test Circuits



Package Outline Dimensions

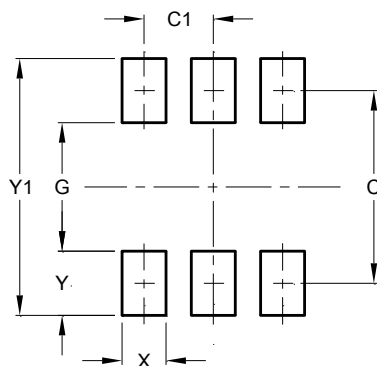
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



SOT26			
Dim	Min	Max	Typ
A1	0.013	0.10	0.05
A2	1.00	1.30	1.10
A3	0.70	0.80	0.75
b	0.35	0.50	0.38
c	0.10	0.20	0.15
D	2.90	3.10	3.00
e	-	-	0.95
e1	-	-	1.90
E	2.70	3.00	2.80
E1	1.50	1.70	1.60
L	0.35	0.55	0.40
a	-	-	8°
a1	-	-	7°
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	2.40
C1	0.95
G	1.60
X	0.55
Y	0.80
Y1	3.20

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